



NTB6412ANT4G Information



For Reference Only

Part Number NTB6412ANT4G
Manufacturer ON Semiconductor

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 100V 58A D2PAK

Package TO-263-3, D2Pak (2 Leads + Tab), TO-263AB

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



Request a Quote

Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









NTB6412ANT4G Specifications

Manufacturer Part Number NTB6412ANT4G Manufacturer ON Semiconductor Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-263-3, D2Pak (2 Leads + Tab), TO-263AB Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 58A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4 V @ 250μA Gate Charge (Qg) (Max) @ Vgs 100nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 3500pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 167W (Tc) Rds On (Max) @ Id, Vgs 18.2 mOhm @ 58A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB		
Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-263-3, D2Pak (2 Leads + Tab), TO-263AB Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 58A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4v @ 250µA Gate Charge (Qg) (Max) @ Vgs 100nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 3500pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 18.2 mOhm @ 58A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Manufacturer Part Number	NTB6412ANT4G
Package TCO-263-3, D2Pak (2 Leads + Tab), TO-263AB Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 58A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 100nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 3500pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 167W (Tc) Rds On (Max) @ Id, Vgs 18.2 mOhm @ 58A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Manufacturer	ON Semiconductor
Package Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 58A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vds 100NC @ 10V Input Capacitance (Ciss) (Max) @ Vds 152 Yes (Max) FET Feature Power Dissipation (Max) 167W (Tc) Rds On (Max) @ Id, Vgs 18.2 mOhm @ 58A, 10V Operating Temperature Supplier Device Package D2PAK Package / Case N-Channel N-CLEAGAS + Tab), TO-263AB	Category	Discrete Semiconductor Products
Series - M-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 58A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 100nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 3500pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 167W (Tc) Rds On (Max) @ Id, Vgs 18.2 mOhm @ 58A, 10V Operating Temperature 55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TOOSC 100V MOSFET (Metal Oxide) 100V 100		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C58A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs100nC @ 10VInput Capacitance (Ciss) (Max) @ Vds3500pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)167W (Tc)Rds On (Max) @ Id, Vgs18.2 mOhm @ 58A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageD2PAKPackage / CaseTO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Package	TO-263-3, D2Pak (2 Leads + Tab), TO-263AB
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C58A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs100nC @ 10VInput Capacitance (Ciss) (Max) @ Vds3500pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)167W (Tc)Rds On (Max) @ Id, Vgs18.2 mOhm @ 58A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageD2PAKPackage / CaseTO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Series	-
Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C58A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs100nC @ 10VInput Capacitance (Ciss) (Max) @ Vds3500pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)167W (Tc)Rds On (Max) @ Id, Vgs18.2 mOhm @ 58A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageD2PAKPackage / CaseTO-263-3, D2Pak (2 Leads + Tab), TO-263AB	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 167W (Tc) Rds On (Max) @ Id, Vgs 18.2 mOhm @ 58A, 10V Operating Temperature Surplier Device Package Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Insumpting Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case 100nC @ 10V 3500pF @ 25V ±20V FET Feature - None Time Time Time Time Time Time Time Tim	Drain to Source Voltage (Vdss)	100V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) +20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 18.2 mOhm @ 58A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Current - Continuous Drain (Id) @ 25°C	58A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) +20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 18.2 mOhm @ 58A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case 100nC @ 10V 1	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 18.2 mOhm @ 58A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)167W (Tc)Rds On (Max) @ Id, Vgs18.2 mOhm @ 58A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageD2PAKPackage / CaseTO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Gate Charge (Qg) (Max) @ Vgs	100nC @ 10V
FET Feature - 167W (Tc) Rds On (Max) @ Id, Vgs 18.2 mOhm @ 58A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Input Capacitance (Ciss) (Max) @ Vds	3500pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 18.2 mOhm @ 58A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs 18.2 mOhm @ 58A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Power Dissipation (Max)	167W (Tc)
Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Rds On (Max) @ Id, Vgs	18.2 mOhm @ 58A, 10V
Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Mounting Type	Surface Mount
	Supplier Device Package	D2PAK
Report errors?	Package / Case	TO-263-3, D2Pak (2 Leads + Tab), TO-263AB
		Report errors?

NTB6412ANT4G Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

NTB6412ANT4G Payment Methods



















NTB6412ANT4G Shipping Methods













If you have any question about NTB6412ANT4G, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com